

Silicon N Channel MOS FET High Speed Power Switching

Rev.1.00

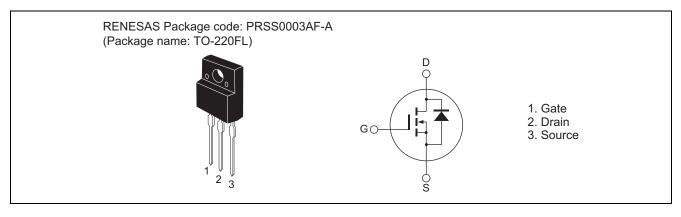
May 23, 2011

Datasheet

### Features

- Low on-state resistance
- $R_{DS(on)} = 2.2 \ \Omega$  typ. (at  $I_D = 1.5 \ A$ ,  $V_{GS} = 10 \ V$ ,  $Ta = 25^{\circ}C$ )
- High speed switching
- Built in fast recovery diode

## Outline



## **Absolute Maximum Ratings**

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	500	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	ID	3	A
Drain peak current	I <sub>D (pulse)</sub> Note1	12	A
Avalanche current	I <sub>AP</sub> Note3	3	А
Channel dissipation	Pch Note 2	30.6	W
Channel to case thermal Impedance	θch-c	4.08	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Pulse width limited by safe operating area.

2. Value at Tc =  $25^{\circ}$ C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C



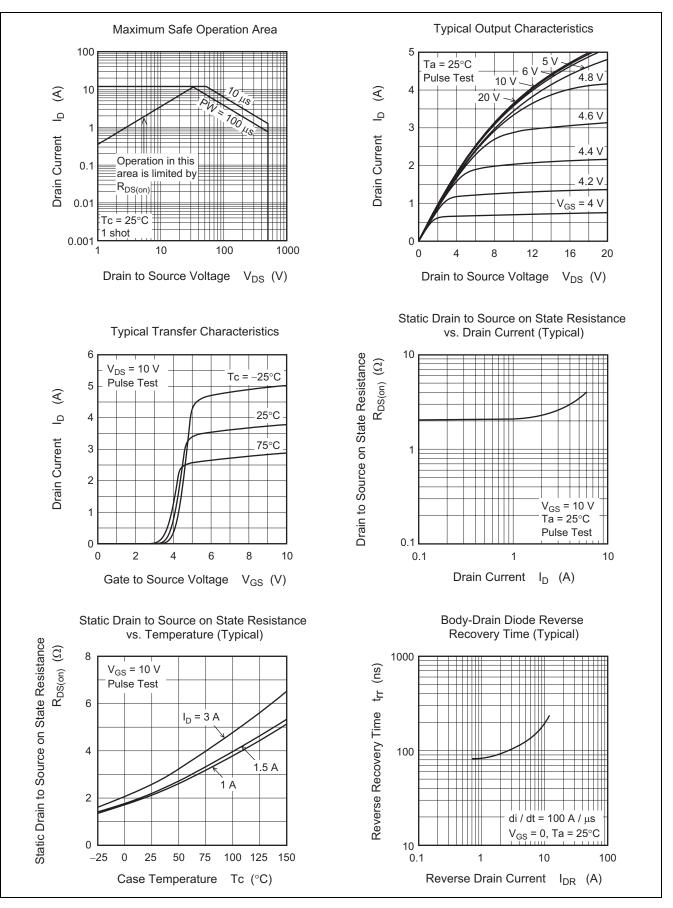
## **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	500	_	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_		10	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_		±0.1	μΑ	$V_{GS}$ = ±30 V, $V_{DS}$ = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	2		4	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS (on)</sub>	_	2.2	2.8	Ω	$I_D$ = 1.5 A, $V_{GS}$ = 10 V <sup>Note 4</sup>
Input capacitance	Ciss	_	265	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	35	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	4.5	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d (on)</sub>	_	6	_	ns	V <sub>DD</sub> = 250 V
Rise time	tr	_	2.5	_	ns	I <sub>D</sub> = 1.5 A
Turn-off delay time	t <sub>d (off)</sub>	—	20	_	ns	V <sub>GS</sub> = 10 V
Fall time	t <sub>f</sub>	—	25	_	ns	Rg = 10 Ω
Total gage charge	Qg	—	10.3		nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs	—	1.5	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	—	5.2	_	nC	I <sub>D</sub> = 3 A
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.9	1.5	V	$I_F = 3 \text{ A}, V_{GS} = 0^{Note 4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	100		ns	$I_F = 3 A, V_{GS} = 0$
						V <sub>DD</sub> = 250 V
						di <sub>F</sub> /dt = 100 A/µs

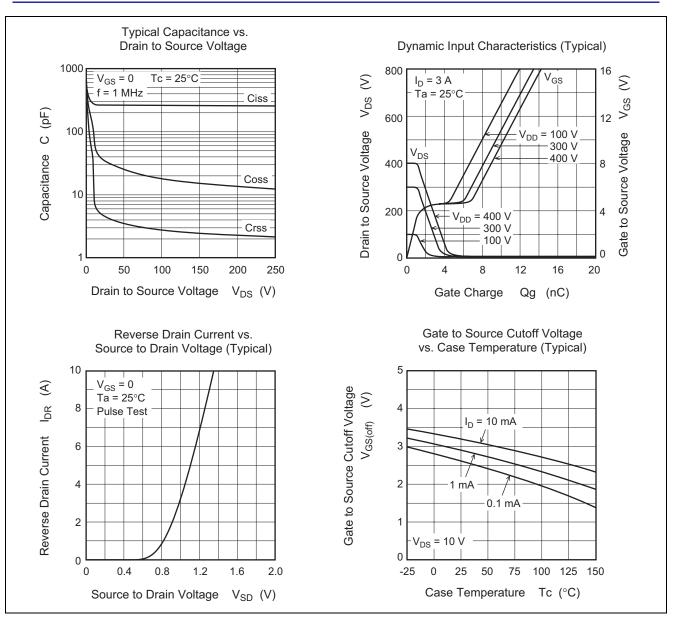
Note: 4. Pulse test



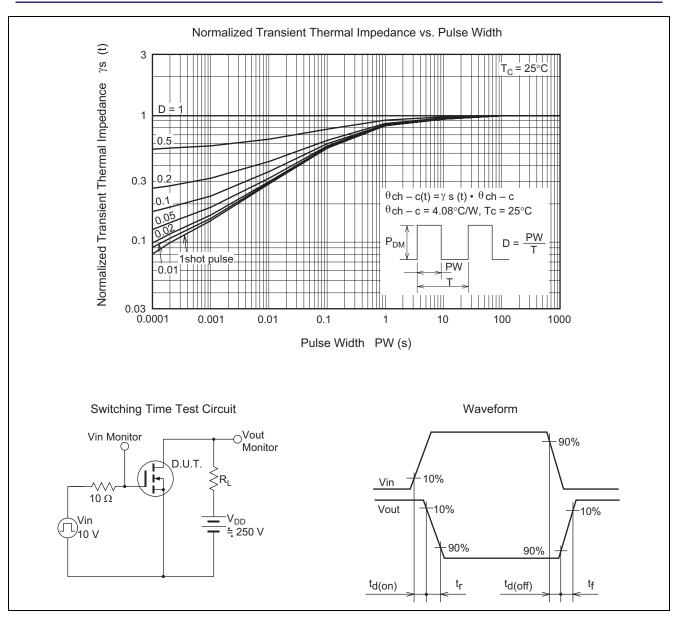
### **Main Characteristics**





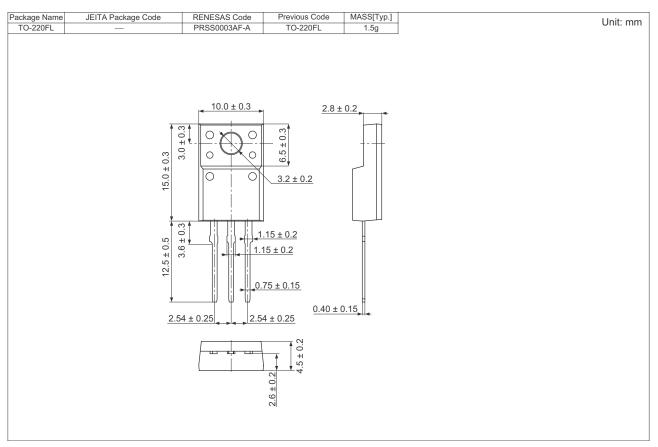








## **Package Dimensions**



# **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
RJL5032DPP-M0-T2	600 pcs	Box (Tube)



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